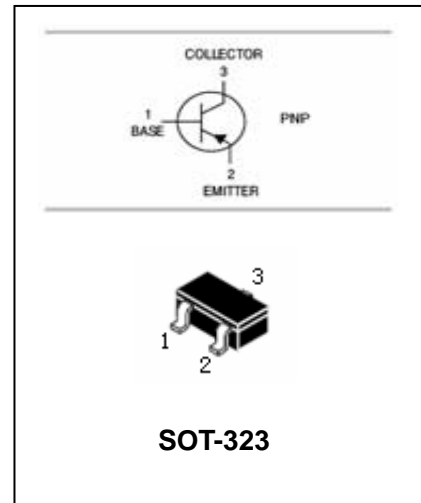


PNP Silicon Epitaxial Planar Transistor

2SA1586W

FEATURES

- High voltage and high current.
- Excellent H_{FE} Linearity.
- High h_{FE} linearity.
- Complementary to 2SC4116.



APPLICATIONS

- Audio frequency general purpose amplifier applications.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1586W	SO/SY/SG	SOT-323

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-150	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~125	$^\circ\text{C}$

PNP Silicon Epitaxial Planar Transistor**2SA1586W****ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-6V, I_C=-2mA$	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$		-0.1	-0.3	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-1mA$	80			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		4	7	pF

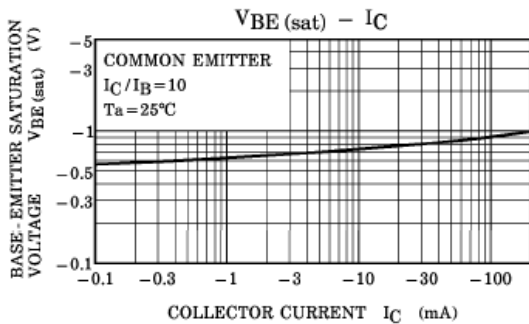
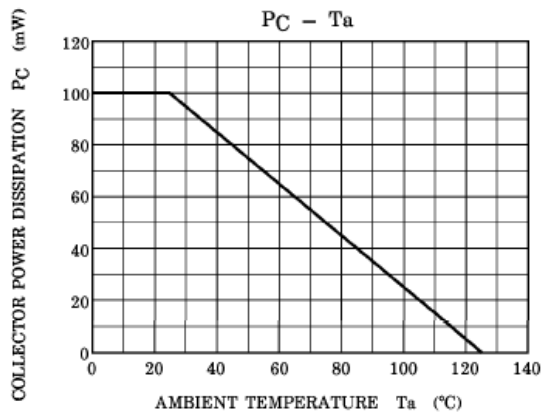
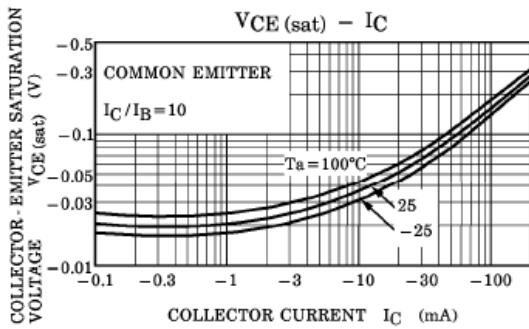
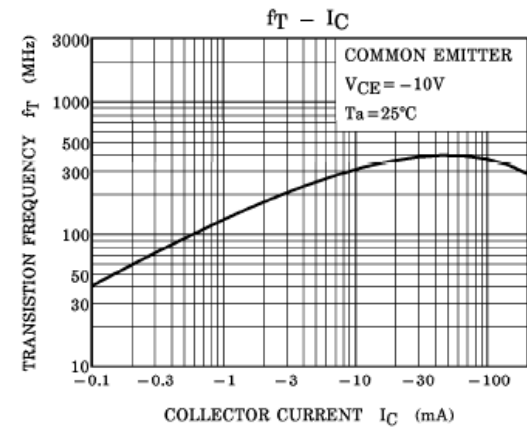
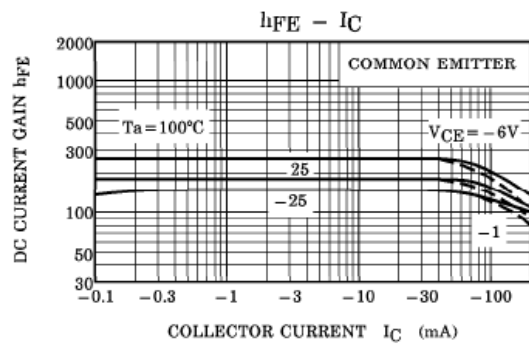
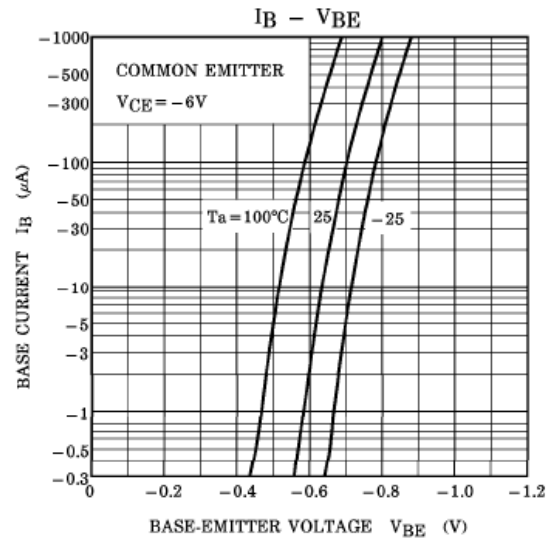
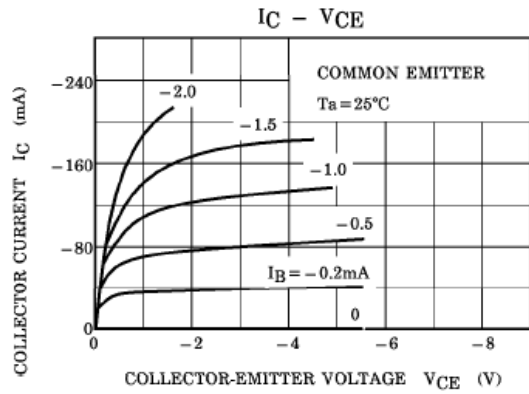
CLASSIFICATION OF h_{FE}

Rank	O	Y	GR
Range	70-140	120-240	200-400
marking	SO	SY	SG

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

PNP Silicon Epitaxial Planar Transistor

2SA1586W



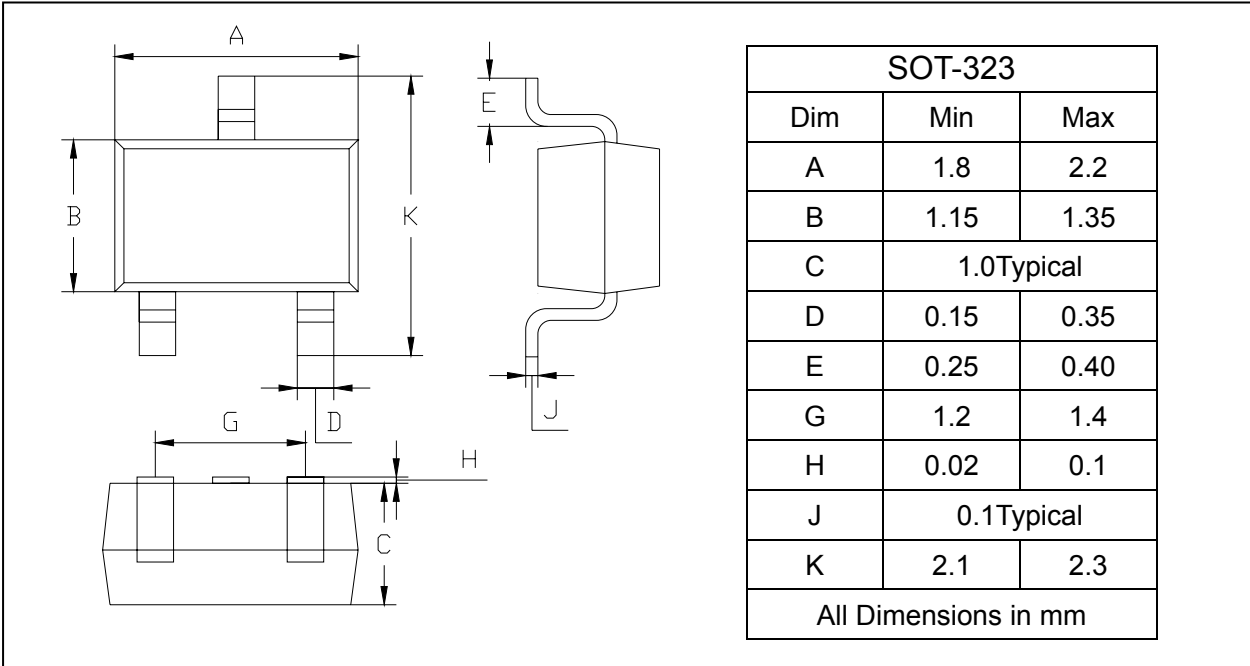
PNP Silicon Epitaxial Planar Transistor

2SA1586W

PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



PACKAGE INFORMATION

Device	Package	Shipping
2SA1586W	SOT-323	3000/Tape&Reel